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- AN - 2003-179087 [18]  
TI - Silicon film etching method for silicon substrate, involves determining starting time of etching naturally oxidized film, during pressure rise in etching chamber  
AB - JP2003001598 NOVELTY - The silicon film on the substrate is etched by subsequently introducing xenon fluoride (XeF<sub>2</sub>) gas in the etching chamber maintained at a predetermined pressure. The naturally oxidized film is removed from the silicon film, when the pressure increases temporarily during etching. The starting time of etching the silicon film is determined to control etching time.  
- USE - For etching silicon substrate, glass substrate and semiconductor integrated circuit.  
- ADVANTAGE - The etching starting time of the silicon film can be detected stably, without being dependent on the thickness of the naturally oxidized film.  
- DESCRIPTION OF DRAWING(S) - The figure shows the graph representing the relationship between the etching elapsed time and pressure in the etching chamber. (Drawing includes non-English language text).  
- (Dwg.7/8)  
IW - SILICON FILM ETCH METHOD SILICON SUBSTRATE DETERMINE START TIME ETCH NATURAL OXIDATION FILM PRESSURE RISE ETCH CHAMBER  
PN - JP2003001598 A 20030108 DW200318 B81C1/00 008pp  
IC - B81C1/00 ;H01L21/3065 ;H01L49/00  
MC - L04-C07D  
- U11-C07A1 U11-C07C1  
DC - L03 Q68 U11  
PA - (SONY) SONY CORP  
AP - JP20010188034 20010621  
PR - JP20010188034 20010621